NSN 5962-01-421-7470

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View Online at https://aerobasegroup.com/nsn/5962-01-421-7470
Body Length:
Between 0.342 inches and 0.358 inches
Body Width:
Between 0.342 inches and 0.358 inches
Body Height:
Between 0.060 inches and 0.100 inches
Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Electrostatic sensitive and burn in and programmable and positive outputs
Inclosure Material:
Ceramic
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Criticality Code Justification:
Cbbl
Case Outline Source And Designator:
C-2 mil-m-38510
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, programmed (pal 16r6a
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
30.00 nanoseconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Pal

Special Features:

Altered item programmed using 14933 81036092 (which is 83149 m38510/81036)using programming instruction 7554044p14

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type And Quantity:
20 leadless
Shelf Life:
N/a
Unit Of Measure:

No

Fiig:

A458a0

Demilitarization: